

Kimberly A Dick

List of Publications by Year in descending order

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182
papers

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186
all docs

186
docs citations

186
times ranked

7349
citing authors

#	ARTICLE	IF	CITATIONS
1	Direct Observations of Twin Formation Dynamics in Binary Semiconductors. ACS Nanoscience Au, 2022, 2, 49-56.	2.0	8
2	Post-nucleation evolution of the liquid–solid interface in nanowire growth. Nanotechnology, 2022, 33, 105607.	1.3	3
3	Experimental Verification of the Work Fluctuation-Dissipation Relation for Information-to-Work Conversion. Physical Review Letters, 2022, 128, 040602.	2.9	12
4	Simulating Vapor–Liquid–Solid Growth of Au-Seeded InGaAs Nanowires. ACS Nanoscience Au, 2022, 2, 239-249.	2.0	7
5	Growth selectivity control of InAs shells on crystal phase engineered GaAs nanowires. Nanoscale Advances, 2022, 4, 3330-3341.	2.2	5
6	Time-resolved photoluminescence studies of single interface wurtzite/zincblende heterostructured InP nanowires. Applied Physics Letters, 2022, 120, .	1.5	2
7	Interface Dynamics in Ag ₃ Cu ₃ P Nanoparticle Heterostructures. Journal of the American Chemical Society, 2022, 144, 248-258.	6.6	10
8	Effects of Parity and Symmetry on the Aharonov–Bohm Phase of a Quantum Ring. Nano Letters, 2022, 22, 334-339.	4.5	5
9	Enabling <i>In Situ</i> Studies of Metal-Organic Chemical Vapor Deposition in a Transmission Electron Microscope. Microscopy and Microanalysis, 2022, 28, 1484-1492.	0.2	11
10	Unraveling the Ultrafast Hot Electron Dynamics in Semiconductor Nanowires. ACS Nano, 2021, 15, 1133-1144.	7.3	18
11	Vapor–solid–solid growth dynamics in GaAs nanowires. Nanoscale Advances, 2021, 3, 5928-5940.	2.2	16
12	Gate control, g factors, and spin-orbit energy of p-type GaSb nanowire quantum dot devices. Physical Review B, 2021, 103, .	1.1	1
13	Symmetry-controlled singlet-triplet transition in a double-barrier quantum ring. Physical Review B, 2021, 104, .	1.1	4
14	Efficient and continuous microwave photoconversion in hybrid cavity-semiconductor nanowire double quantum dot diodes. Nature Communications, 2021, 12, 5130.	5.8	17
15	Compositional Correlation between the Nanoparticle and the Growing Au-Assisted In _x Ga _{1-x} As Nanowire. Journal of Physical Chemistry Letters, 2021, 12, 7590-7595.	2.1	12
16	Unraveling electronic band structure of narrow-bandgap π nanojunctions in heterostructured nanowires. Physical Chemistry Chemical Physics, 2021, 23, 25019-25023.	1.3	6
17	Self-selective formation of ordered 1D and 2D GaBi structures on wurtzite GaAs nanowire surfaces. Nature Communications, 2021, 12, 5990.	5.8	3
18	Measuring Surface Tension of III-V Nanowire Au-Catalyst Droplets with an E-field. Microscopy and Microanalysis, 2021, 27, 27-28.	0.2	0

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19	Atomically sharp, crystal phase defined GaAs quantum dots. Applied Physics Letters, 2021, 119, .	1.5	7
20	Two-dimensional electron gas at wurtzite/zinc-blende InP interfaces induced by modulation doping. Applied Physics Letters, 2020, 116, 232103.	1.5	9
21	Limits of III-V Nanowire Growth Based on Droplet Dynamics. Journal of Physical Chemistry Letters, 2020, 11, 2949-2954.	2.1	14
22	Magnetic-Field-Independent Subgap States in Hybrid Rashba Nanowires. Physical Review Letters, 2020, 125, 017701.	2.9	38
23	Effect of Radius on Crystal Structure Selection in III-V Nanowire Growth. Crystal Growth and Design, 2020, 20, 5373-5379.	1.4	7
24	In situ metal-organic chemical vapour deposition growth of III-V semiconductor nanowires in the Lund environmental transmission electron microscope. Semiconductor Science and Technology, 2020, 35, 034004.	1.0	20
25	Independent Control of Nucleation and Layer Growth in Nanowires. ACS Nano, 2020, 14, 3868-3875.	7.3	31
26	Selective tuning of spin-orbital Kondo contributions in parallel-coupled quantum dots. Physical Review B, 2020, 101, .	1.1	2
27	Non-resonant Raman scattering of wurtzite GaAs and InP nanowires. Optics Express, 2020, 28, 11016.	1.7	1
28	Spectroscopy of the superconducting proximity effect in nanowires using integrated quantum dots. Communications Physics, 2019, 2, .	2.0	28
29	In situ analysis of catalyst composition during gold catalyzed GaAs nanowire growth. Nature Communications, 2019, 10, 4577.	5.8	49
30	Kinetics of Au-Ga Droplet Mediated Decomposition of GaAs Nanowires. Nano Letters, 2019, 19, 3498-3504.	4.5	18
31	Simultaneous Growth of Pure Wurtzite and Zinc Blende Nanowires. Nano Letters, 2019, 19, 2723-2730.	4.5	13
32	Nanowire morphology and particle phase control by tuning the In concentration of the foreign metal nanoparticle. Nanotechnology, 2019, 30, 054005.	1.3	4
33	Simulation of GaAs Nanowire Growth and Crystal Structure. Nano Letters, 2019, 19, 1197-1203.	4.5	27
34	Sb Incorporation in Wurtzite and Zinc Blende InAs _{1-x} Sb _x Branches on InAs Template Nanowires. Small, 2018, 14, e1703785.	5.2	5
35	Hydrogen-assisted spark discharge generated metal nanoparticles to prevent oxide formation. Aerosol Science and Technology, 2018, 52, 347-358.	1.5	31
36	Temperature dependent electronic band structure of wurtzite GaAs nanowires. Nanoscale, 2018, 10, 1481-1486.	2.8	16

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37	Spatial Control of Multiphoton Electron Excitations in InAs Nanowires by Varying Crystal Phase and Light Polarization. <i>Nano Letters</i> , 2018, 18, 907-915.	4.5	11
38	Atomic-Resolution Spectrum Imaging of Semiconductor Nanowires. <i>Nano Letters</i> , 2018, 18, 1557-1563.	4.5	21
39	Spectroscopy and level detuning of few-electron spin states in parallel InAs quantum dots. <i>Physical Review B</i> , 2018, 98, .	1.1	6
40	Understanding GaAs Nanowire Growth in the Ag-Au Seed Materials System. <i>Crystal Growth and Design</i> , 2018, 18, 6702-6712.	1.4	5
41	Branched InAs nanowire growth by droplet confinement. <i>Applied Physics Letters</i> , 2018, 113, 123104.	1.5	11
42	Tuning the Two-Electron Hybridization and Spin States in Parallel-Coupled InAs Quantum Dots. <i>Physical Review Letters</i> , 2018, 121, 156802.	2.9	14
43	Realization of Wurtzite GaSb Using InAs Nanowire Templates. <i>Advanced Functional Materials</i> , 2018, 28, 1800512.	7.8	13
44	Radial band bending at wurtzite-zinc-blende GaAs interfaces. <i>Nano Futures</i> , 2018, 2, 035002.	1.0	7
45	Kinetic Engineering of Wurtzite and Zinc-Blende AlSb Shells on InAs Nanowires. <i>Nano Letters</i> , 2018, 18, 5775-5781.	4.5	6
46	Polarity and growth directions in Sn-seeded GaSb nanowires. <i>Nanoscale</i> , 2017, 9, 3159-3168.	2.8	24
47	Annealing of Au, Ag and Au-Ag alloy nanoparticle arrays on GaAs (100) and (111)B. <i>Nanotechnology</i> , 2017, 28, 205702.	1.3	11
48	Crystal Structure Induced Preferential Surface Alloying of Sb on Wurtzite/Zinc Blende GaAs Nanowires. <i>Nano Letters</i> , 2017, 17, 3634-3640.	4.5	14
49	Direct nucleation, morphology and compositional tuning of InAs _{1-x} Sb _x nanowires on InAs (111) B substrates. <i>Nanotechnology</i> , 2017, 28, 165601.	1.3	23
50	Conduction Band Offset and Polarization Effects in InAs Nanowire Polytype Junctions. <i>Nano Letters</i> , 2017, 17, 902-908.	4.5	34
51	Electronic Structure Changes Due to Crystal Phase Switching at the Atomic Scale Limit. <i>ACS Nano</i> , 2017, 11, 10519-10528.	7.3	15
52	Thermodynamic Stability of Gold-Assisted InAs Nanowire Growth. <i>Journal of Physical Chemistry C</i> , 2017, 121, 21678-21684.	1.5	11
53	Imaging Atomic Scale Dynamics on III-V Nanowire Surfaces During Electrical Operation. <i>Scientific Reports</i> , 2017, 7, 12790.	1.6	5
54	Parallel-Coupled Quantum Dots in InAs Nanowires. <i>Nano Letters</i> , 2017, 17, 7847-7852.	4.5	27

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55	Micro-Raman spectroscopy for the detection of stacking fault density in InAs and GaAs nanowires. Physical Review B, 2017, 96, .	1.1	6
56	Characterization of individual stacking faults in aWurtzite GaAs nanowire by nanobeam X-ray diffraction. Journal of Synchrotron Radiation, 2017, 24, 981-990.	1.0	9
57	Demonstration of Sn-seeded GaSb homo- and GaAs-GaSb heterostructural nanowires. Nanotechnology, 2016, 27, 175602.	1.3	11
58	Nondestructive Complete Mechanical Characterization of Zinc Blende and Wurtzite GaAs Nanowires Using Time-Resolved Pump-Probe Spectroscopy. Nano Letters, 2016, 16, 4792-4798.	4.5	25
59	Sn-seeded GaAs nanowires grown by MOVPE. Nanotechnology, 2016, 27, 215603.	1.3	7
60	Electron-hole interactions in coupled InAs-GaSb quantum dots based on nanowire crystal phase templates. Physical Review B, 2016, 94, .	1.1	16
61	Hybrid ZnO/GaN distributed Bragg reflectors grown by plasma-assisted molecular beam epitaxy. APL Materials, 2016, 4, 086106.	2.2	7
62	Palladium seeded GaAs nanowires. Journal of Materials Research, 2016, 31, 175-185.	1.2	10
63	Single-electron transport in InAs nanowire quantum dots formed by crystal phase engineering. Physical Review B, 2016, 93, .	1.1	45
64	InAs nanowire GAA n-MOSFETs with 12-15 nm diameter. , 2016, , .		14
65	Schottky barrier and contact resistance of InSb nanowire field-effect transistors. Nanotechnology, 2016, 27, 275204.	1.3	14
66	Can antimonide-based nanowires form wurtzite crystal structure?. Nanoscale, 2016, 8, 2778-2786.	2.8	20
67	Interface dynamics and crystal phase switching in GaAs nanowires. Nature, 2016, 531, 317-322.	13.7	272
68	Wurtzite GaAs Quantum Wires: One-Dimensional Subband Formation. Nano Letters, 2016, 16, 2774-2780.	4.5	23
69	Silver as Seed-Particle Material for GaAs Nanowires Dictating Crystal Phase and Growth Direction by Substrate Orientation. Nano Letters, 2016, 16, 2181-2188.	4.5	33
70	Polytype Attainability in III-V Semiconductor Nanowires. Crystal Growth and Design, 2016, 16, 371-379.	1.4	23
71	Phase Transformation in Radially Merged Wurtzite GaAs Nanowires. Crystal Growth and Design, 2015, 15, 4795-4803.	1.4	27
72	Sn-Seeded GaAs Nanowires as Self-Assembled Radial Junctions. Nano Letters, 2015, 15, 3757-3762.	4.5	25

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73	Selective GaSb radial growth on crystal phase engineered InAs nanowires. <i>Nanoscale</i> , 2015, 7, 10472-10481.	2.8	42
74	Characterization of Ambipolar GaSb/InAs Core-Shell Nanowires by Thermovoltage Measurements. <i>ACS Nano</i> , 2015, 9, 7033-7040.	7.3	15
75	Electrical and Surface Properties of InAs/InSb Nanowires Cleaned by Atomic Hydrogen. <i>Nano Letters</i> , 2015, 15, 4865-4875.	4.5	35
76	Confinement in Thickness-Controlled GaAs Polytype Nanodots. <i>Nano Letters</i> , 2015, 15, 2652-2656.	4.5	62
77	Scanning Tunneling Spectroscopy on InAs-GaSb Esaki Diode Nanowire Devices during Operation. <i>Nano Letters</i> , 2015, 15, 3684-3691.	4.5	16
78	Atomic Scale Surface Structure and Morphology of InAs Nanowire Crystal Superlattices: The Effect of Epitaxial Overgrowth. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 5748-5755.	4.0	23
79	Crystal phase control in GaAs nanowires: opposing trends in the Ga- and As-limited growth regimes. <i>Nanotechnology</i> , 2015, 26, 301001.	1.3	43
80	Magnetoresistance in Mn ion-implanted GaAs:Zn nanowires. <i>Applied Physics Letters</i> , 2014, 104, 153112.	1.5	8
81	Atomic-Scale Variability and Control of III-V Nanowire Growth Kinetics. <i>Science</i> , 2014, 343, 281-284.	6.0	87
82	Observation of type-II recombination in single wurtzite/zinc-blende GaAs heterojunction nanowires. <i>Physical Review B</i> , 2014, 89, .	1.1	60
83	Enhanced sputtering and incorporation of Mn in implanted GaAs and ZnO nanowires. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 394003.	1.3	24
84	Electronic and Structural Differences between Wurtzite and Zinc Blende InAs Nanowire Surfaces: Experiment and Theory. <i>ACS Nano</i> , 2014, 8, 12346-12355.	7.3	78
85	Realization of single and double axial InSb-GaSb heterostructure nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 269-273.	1.2	3
86	Semiconductor nanostructures enabled by aerosol technology. <i>Frontiers of Physics</i> , 2014, 9, 398-418.	2.4	19
87	Morphology and composition controlled Ga _x In _{1-x} Sb nanowires: understanding ternary antimonide growth. <i>Nanoscale</i> , 2014, 6, 1086-1092.	2.8	19
88	Crystal structure tuning in GaAs nanowires using HCl. <i>Nanoscale</i> , 2014, 6, 8257.	2.8	9
89	Crystal Phase-Dependent Nanophotonic Resonances in InAs Nanowire Arrays. <i>Nano Letters</i> , 2014, 14, 5650-5655.	4.5	26
90	Metal-seeded growth of III-V semiconductor nanowires: towards gold-free synthesis. <i>Nanoscale</i> , 2014, 6, 3006-3021.	2.8	78

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91	Electrical properties of GaSb/InAsSb core/shell nanowires. <i>Nanotechnology</i> , 2014, 25, 425201.	1.3	32
92	High resolution scanning gate microscopy measurements on InAs/GaSb nanowire Esaki diode devices. <i>Nano Research</i> , 2014, 7, 877-887.	5.8	15
93	Time-Resolved X-ray Diffraction Investigation of the Modified Phonon Dispersion in InSb Nanowires. <i>Nano Letters</i> , 2014, 14, 541-546.	4.5	16
94	Measurements of light absorption efficiency in InSb nanowires. <i>Structural Dynamics</i> , 2014, 1, 014502.	0.9	4
95	A General Approach for Sharp Crystal Phase Switching in InAs, GaAs, InP, and GaP Nanowires Using Only Group V Flow. <i>Nano Letters</i> , 2013, 13, 4099-4105.	4.5	156
96	Direct Imaging of Atomic Scale Structure and Electronic Properties of GaAs Wurtzite and Zinc Blende Nanowire Surfaces. <i>Nano Letters</i> , 2013, 13, 4492-4498.	4.5	63
97	Large Thermoelectric Power Factor Enhancement Observed in InAs Nanowires. <i>Nano Letters</i> , 2013, 13, 4080-4086.	4.5	107
98	Conductance Enhancement of InAs/InP Heterostructure Nanowires by Surface Functionalization with Oligo(phenylene vinylene)s. <i>ACS Nano</i> , 2013, 7, 4111-4118.	7.3	16
99	High-Current GaSb/InAs(Sb) Nanowire Tunnel Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2013, 34, 211-213.	2.2	108
100	Strategies To Control Morphology in Hybrid Group III-V/Group IV Heterostructure Nanowires. <i>Nano Letters</i> , 2013, 13, 903-908.	4.5	63
101	Cu particle seeded InP-InAs axial nanowire heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 850-854.	1.2	5
102	Diameter Limitation in Growth of III-Sb-Containing Nanowire Heterostructures. <i>ACS Nano</i> , 2013, 7, 3668-3675.	7.3	45
103	Control of composition and morphology in InGaAs nanowires grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2013, 383, 158-165.	0.7	39
104	Self-catalyzed MBE grown GaAs/GaSb core-shell nanowires in ZB and WZ crystal structures. <i>Nanotechnology</i> , 2013, 24, 405601.	1.3	21
105	Control and understanding of kink formation in InAs-InP heterostructure nanowires. <i>Nanotechnology</i> , 2013, 24, 345601.	1.3	14
106	Zincblende-wurtzite interface improvement by group III loading in Au-seeded GaAs nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 855-859.	1.2	13
107	Phonon Transport and Thermoelectricity in Defect-Engineered InAs Nanowires. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1404, 36.	0.1	6
108	A cathodoluminescence study of the influence of the seed particle preparation method on the optical properties of GaAs nanowires. <i>Nanotechnology</i> , 2012, 23, 265704.	1.3	7

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109	Influence of doping on the electronic transport in GaSb/InAs(Sb) nanowire tunnel devices. Applied Physics Letters, 2012, 101, 043508.	1.5	33
110	High current density InAsSb/GaSb tunnel field effect transistors. , 2012, , .		7
111	Demonstration of Defect-Free and Composition Tunable Ga _x In _{1-x} Sb Nanowires. Nano Letters, 2012, 12, 4914-4919.	4.5	44
112	High-Performance InAs Nanowire MOSFETs. IEEE Electron Device Letters, 2012, 33, 791-793.	2.2	60
113	Faceting, composition and crystal phase evolution in III ^V antimonide nanowire heterostructures revealed by combining microscopy techniques. Nanotechnology, 2012, 23, 095702.	1.3	95
114	Growth of InAs/InP core-shell nanowires with various pure crystal structures. Nanotechnology, 2012, 23, 285601.	1.3	50
115	Uniform and position-controlled InAs nanowires on 2 nd Si substrates for transistor applications. Nanotechnology, 2012, 23, 015302.	1.3	36
116	Carrier control and transport modulation in GaSb/InAsSb core/shell nanowires. Applied Physics Letters, 2012, 101, .	1.5	43
117	Controlling the Abruptness of Axial Heterojunctions in III ^V Nanowires: Beyond the Reservoir Effect. Nano Letters, 2012, 12, 3200-3206.	4.5	121
118	Electrical properties of InAs _{1-x} Sbx and InSb nanowires grown by molecular beam epitaxy. Applied Physics Letters, 2012, 100, 232105.	1.5	56
119	Highly controlled InAs nanowires on Si(111) wafers by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 206-209.	0.8	17
120	Combinatorial Approaches to Understanding Polytypism in III ^V Nanowires. ACS Nano, 2012, 6, 6142-6149.	7.3	59
121	Simultaneous growth mechanisms for Cu-seeded InP nanowires. Nano Research, 2012, 5, 297-306.	5.8	25
122	High crystal quality wurtzite-zinc blende heterostructures in metal-organic vapor phase epitaxy-grown GaAs nanowires. Nano Research, 2012, 5, 470-476.	5.8	51
123	Crystal structure control in Au-free self-seeded InSb wire growth. Nanotechnology, 2011, 22, 145603.	1.3	45
124	Recent advances in semiconductor nanowire heterostructures. CrystEngComm, 2011, 13, 7175.	1.3	104
125	Thermal conductivity of indium arsenide nanowires with wurtzite and zinc blende phases. Physical Review B, 2011, 83, .	1.1	96
126	Formation of the Axial Heterojunction in GaSb/InAs(Sb) Nanowires with High Crystal Quality. Crystal Growth and Design, 2011, 11, 4588-4593.	1.4	35

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127	Unit Cell Structure of Crystal Polytypes in InAs and InSb Nanowires. Nano Letters, 2011, 11, 1483-1489.	4.5	117
128	High Current Density Esaki Tunnel Diodes Based on GaSb-InAsSb Heterostructure Nanowires. Nano Letters, 2011, 11, 4222-4226.	4.5	106
129	High quality InAs and GaSb thin layers grown on Si (111). Journal of Crystal Growth, 2011, 332, 12-16.	0.7	54
130	Effects of Crystal Phase Mixing on the Electrical Properties of InAs Nanowires. Nano Letters, 2011, 11, 2424-2429.	4.5	211
131	Introduction to the Issue on Nanowires. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 763-765.	1.9	0
132	Epitaxial InP nanowire growth from Cu seed particles. Journal of Crystal Growth, 2011, 315, 134-137.	0.7	17
133	Wurtzite-zincblende superlattices in InAs nanowires using a supply interruption method. Nanotechnology, 2011, 22, 265606.	1.3	46
134	Parameter space mapping of InAs nanowire crystal structure. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 04D103.	0.6	43
135	Enhanced Sb incorporation in InAsSb nanowires grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2011, 98, .	1.5	56
136	Diameter reduction of nanowire tunnel heterojunctions using in situ annealing. Applied Physics Letters, 2011, 99, 203101.	1.5	13
137	A comparative study of the effect of gold seed particle preparation method on nanowire growth. Nano Research, 2010, 3, 506-519.	5.8	43
138	Control of III-V nanowire crystal structure by growth parameter tuning. Semiconductor Science and Technology, 2010, 25, 024009.	1.0	219
139	Gold-free GaAs/GaSb heterostructure nanowires grown on silicon. Applied Physics Letters, 2010, 96, .	1.5	83
140	Branched nanotrees with immobilized acetylcholine esterase for nanobiosensor applications. Nanotechnology, 2010, 21, 055102.	1.3	10
141	Crystal Phase Engineering in Single InAs Nanowires. Nano Letters, 2010, 10, 3494-3499.	4.5	234
142	Diameter Dependence of the Wurtzite-Zinc Blende Transition in InAs Nanowires. Journal of Physical Chemistry C, 2010, 114, 3837-3842.	1.5	129
143	InAs/GaSb Heterostructure Nanowires for Tunnel Field-Effect Transistors. Nano Letters, 2010, 10, 4080-4085.	4.5	161
144	Gold-free growth of GaAs nanowires on silicon: arrays and polytypism. Nanotechnology, 2010, 21, 385602.	1.3	149

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145	The electrical and structural properties of n-type InAs nanowires grown from metal-organic precursors. <i>Nanotechnology</i> , 2010, 21, 205703.	1.3	86
146	Microphotoluminescence studies of tunable wurtzite InAs _{0.85} P _{0.15} quantum dots embedded in wurtzite InP nanowires. <i>Physical Review B</i> , 2009, 80, .	1.1	18
147	Preferential Interface Nucleation: An Expansion of the VLS Growth Mechanism for Nanowires. <i>Advanced Materials</i> , 2009, 21, 153-165.	11.1	309
148	Generation of size-selected gold nanoparticles by spark discharge for growth of epitaxial nanowires. <i>Gold Bulletin</i> , 2009, 42, 20-26.	3.2	51
149	The use of gold for fabrication of nanowire structures. <i>Gold Bulletin</i> , 2009, 42, 172-181.	3.2	61
150	Controlled polytypic and twin-plane superlattices in InAs nanowires. <i>Nature Nanotechnology</i> , 2009, 4, 50-55.	15.6	646
151	Effects of Supersaturation on the Crystal Structure of Gold Seeded III-V Nanowires. <i>Crystal Growth and Design</i> , 2009, 9, 766-773.	1.4	147
152	InSb heterostructure nanowires: MOVPE growth under extreme lattice mismatch. <i>Nanotechnology</i> , 2009, 20, 495606.	1.3	121
153	High-Quality InAs/InSb Nanowire Heterostructures Grown by Metal-Organic Vapor-Phase Epitaxy. <i>Small</i> , 2008, 4, 878-882.	5.2	160
154	GaAs/GaSb nanowire heterostructures grown by MOVPE. <i>Journal of Crystal Growth</i> , 2008, 310, 4115-4121.	0.7	85
155	Characterization of GaSb nanowires grown by MOVPE. <i>Journal of Crystal Growth</i> , 2008, 310, 5119-5122.	0.7	45
156	Effects of growth conditions on the crystal structure of gold-seeded GaP nanowires. <i>Journal of Crystal Growth</i> , 2008, 310, 5102-5105.	0.7	15
157	A review of nanowire growth promoted by alloys and non-alloying elements with emphasis on Au-assisted III-V nanowires. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2008, 54, 138-173.	1.8	249
158	Surface-enhanced Raman scattering of rhodamine 6G on nanowire arrays decorated with gold nanoparticles. <i>Nanotechnology</i> , 2008, 19, 275712.	1.3	62
159	Precursor evaluation for in situ InP nanowire doping. <i>Nanotechnology</i> , 2008, 19, 445602.	1.3	92
160	Control of GaP and GaAs Nanowire Morphology through Particle and Substrate Chemical Modification. <i>Nano Letters</i> , 2008, 8, 4087-4091.	4.5	35
161	Tip-enhanced Raman scattering of p-thiocresol molecules on individual gold nanoparticles. <i>Applied Physics Letters</i> , 2008, 92, 093110.	1.5	35
162	Directed Growth of Branched Nanowire Structures. <i>MRS Bulletin</i> , 2007, 32, 127-133.	1.7	40

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163	Electrospraying of colloidal nanoparticles for seeding of nanostructure growth. <i>Nanotechnology</i> , 2007, 18, 105304.	1.3	29
164	Understanding the 3D structure of GaAs nanowires. <i>Nanotechnology</i> , 2007, 18, 485717.	1.3	41
165	Height-controlled nanowire branches on nanotrees using a polymer mask. <i>Nanotechnology</i> , 2007, 18, 035601.	1.3	14
166	Size-selected compound semiconductor quantum dots by nanoparticle conversion. <i>Nanotechnology</i> , 2007, 18, 105306.	1.3	3
167	The Morphology of Axial and Branched Nanowire Heterostructures. <i>Nano Letters</i> , 2007, 7, 1817-1822.	4.5	175
168	InAs nanowires grown by MOVPE. <i>Journal of Crystal Growth</i> , 2007, 298, 631-634.	0.7	33
169	High-speed Nanometer-scale Imaging for Studies of Nanowire Mechanics. <i>Small</i> , 2007, 3, 1699-1702.	5.2	10
170	Targeted deposition of Au aerosol nanoparticles on vertical nanowires for the creation of nanotrees. <i>Journal of Nanoparticle Research</i> , 2007, 9, 1211-1216.	0.8	10
171	Growth related aspects of epitaxial nanowires. <i>Nanotechnology</i> , 2006, 17, S355-S361.	1.3	100
172	Position-Controlled Interconnected InAs Nanowire Networks. <i>Nano Letters</i> , 2006, 6, 2842-2847.	4.5	85
173	Optimization of Au-assisted InAs nanowires grown by MOVPE. <i>Journal of Crystal Growth</i> , 2006, 297, 326-333.	0.7	67
174	Improving InAs nanotree growth with composition-controlled Au-In nanoparticles. <i>Nanotechnology</i> , 2006, 17, 1344-1350.	1.3	35
175	CRYSTAL STRUCTURE OF BRANCHED EPITAXIAL III-V NANOTREES. <i>Nano</i> , 2006, 01, 139-151.	0.5	12
176	A New Understanding of Au-Assisted Growth of III-V Semiconductor Nanowires. <i>Advanced Functional Materials</i> , 2005, 15, 1603-1610.	7.8	139
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